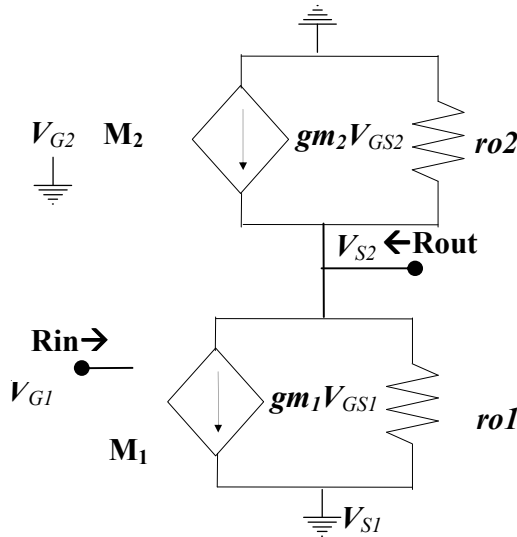


### Small Signal Practice Problem Solutions

Notice, for the scope of EE 40, the solutions here ignore the  $V_{bs}$  and  $g_{mb}$ .

Intuitively, you can assume  $r_o$  to be  $0.5 \text{ M}\Omega$  (high) while  $\frac{1}{g_m}$  is around  $0.5 \text{ k}\Omega$  (low).

(a)  $R_L$  and  $R_S$  omitted for clarity.



(a)

$$r_{in} = \infty$$

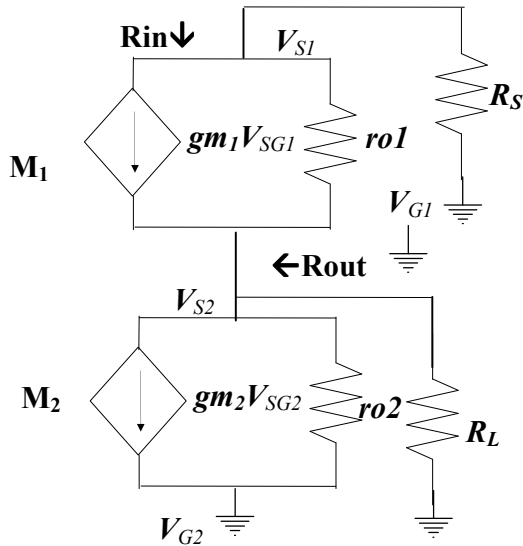
$$r_{out} = \left( \frac{1}{g_{m2}} \right) // r_{o1}$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is low; thus, voltage out

Hence, amplifier is best characterized by a voltage amplifier.

(b) Notice  $M_1$  is a PMOS, so current is  $g_{m1}V_{SG1}$



(b)

$$r_{in} = \frac{r_{o1} + \left( \frac{1}{g_{m2}} // R_L \right)}{g_{m1} \cdot r_{o1}} \approx \frac{r_{o1}}{g_{m1} \cdot r_{o1}} = \frac{1}{g_{m1}}$$

$$r_{out} = \frac{1}{g_{m2}} // (r_{o1} + R_S + g_{m1} \cdot r_{o1} \cdot R_S)$$

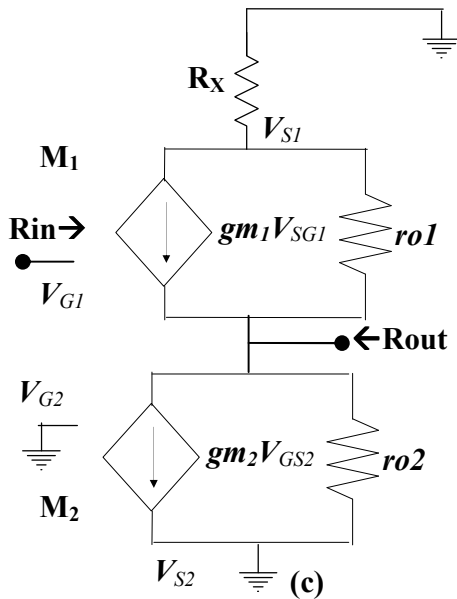
$$r_{out} \approx \frac{1}{g_{m2}}$$

$r_{in}$  is low; thus, current in

$r_{out}$  is low; thus, voltage out

Hence, amplifier is best characterized by a transresistance amplifier

(c)



$$r_{in} = \infty$$

$$r_{out} = (r_{o1} + R_X + g_{m1} \cdot r_{o1} \cdot R_X) \parallel r_{o2}$$

The lowest that  $r_{out}$  can be in value is

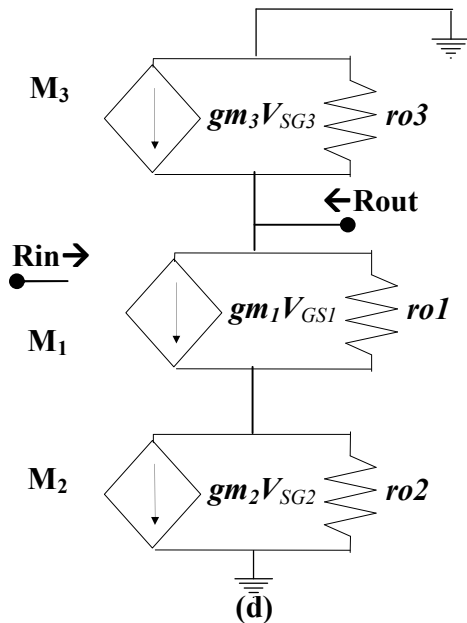
when  $R_X = 0$ . Hence,  $r_{out} \geq \frac{r_o}{2}$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is high; thus, current out

Hence, amplifier is best characterized by a transconductance amplifier

(d)



$$r_{in} = \infty$$

$$r_{out} = r_{o3} \parallel \left( r_{o1} + \frac{1}{g_{m2}} + g_{m1} \cdot r_{o1} \cdot \frac{1}{g_{m2}} \right)$$

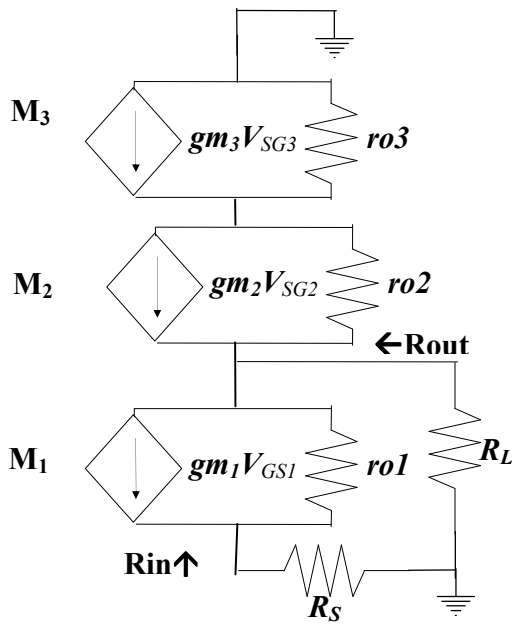
$$r_{out} \approx r_{o3} \parallel (2 \cdot r_{o1})$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is high; thus, current out

Hence, amplifier is best characterized by a transconductance amplifier

(e)



$$r_{in} = \frac{r_{o1} + (r_{o2} + r_{o3} + g_{m2} \cdot r_{o2} \cdot r_{o3}) \parallel R_L}{g_{m1} \cdot r_{o1}}$$

The value for  $r_{in}$  depends heavily on  $R_L$ . Let's assume that  $R_L \ll r_o$ . Hence,

$$r_{out} = (r_{o1} + R_S + g_{m1} \cdot r_{o1} \cdot R_S) \parallel (r_{o2} + r_{o3} + g_{m2} \cdot r_{o2} \cdot r_{o3})$$

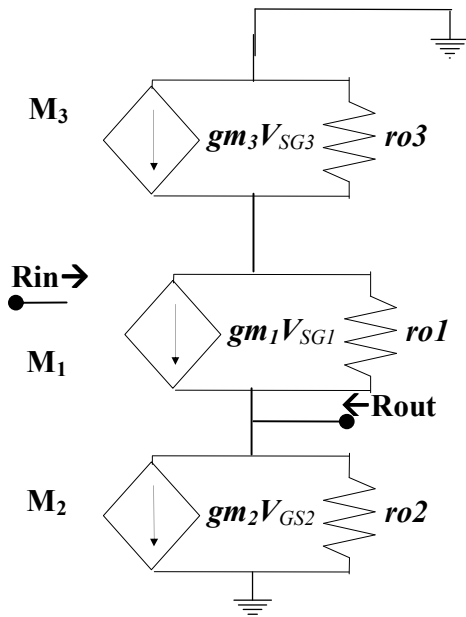
The lowest that  $r_{out}$  can be in value is when  $R_S = 0$ . Hence,  $r_{out} \geq r_{o1}$

$r_{in}$  is low; thus, current in

$r_{out}$  is high; thus, current out

Hence, amplifier is best characterized by a current amplifier

(f)



$$r_{in} = \infty$$

$$r_{out} = \frac{1}{g_{m2}} \parallel \left( r_{o1} + \frac{1}{g_{m3}} + g_{m1} \cdot r_{o1} \cdot \frac{1}{g_{m3}} \right)$$

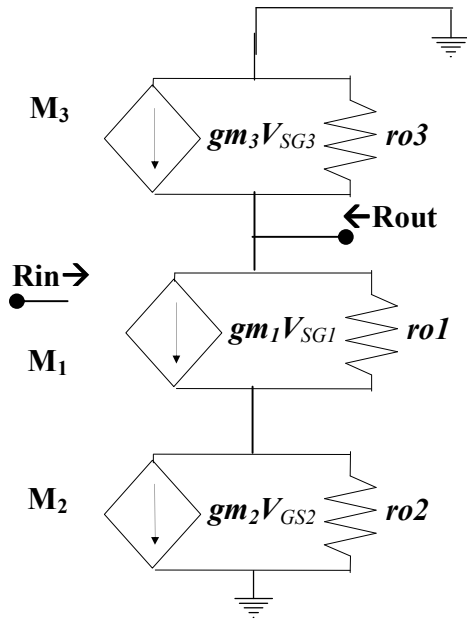
$$r_{out} \approx \frac{1}{g_{m2}}$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is low; thus, voltage out

Hence, amplifier is best characterized by a voltage amplifier

(g)



$$r_{in} = \infty$$

$$r_{out} = \frac{1}{g_{m3}} \parallel \frac{r_{o1} + \frac{1}{g_{m2}}}{g_{m1} \cdot r_{o1}}$$

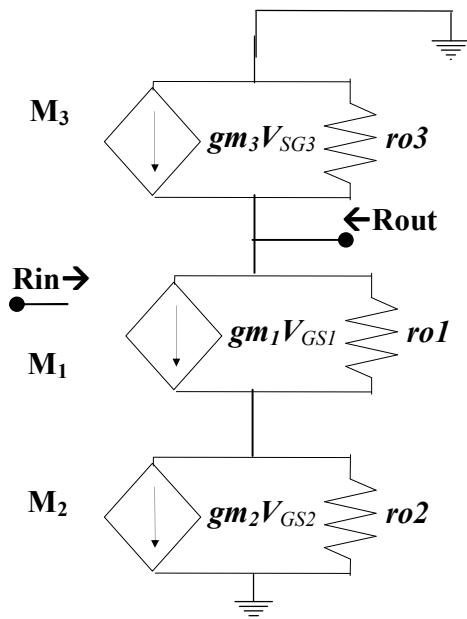
$$r_{out} \approx \frac{1}{g_{m3}} \parallel \frac{1}{g_{m1}}$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is low; thus, voltage out

Hence, amplifier is best characterized by a voltage amplifier

(h)



$$r_{in} = \infty$$

$$r_{out} = r_{o3} \parallel (r_{o1} + r_{o2} + g_{m1} \cdot r_{o1} \cdot r_{o2})$$

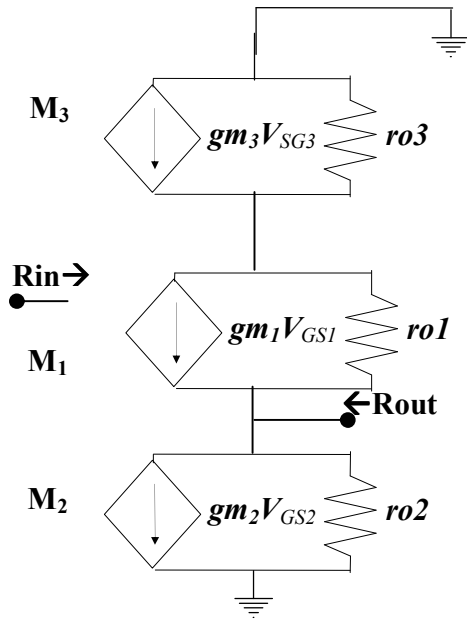
$$r_{out} \approx r_{o3}$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is high; thus, current out

Hence, amplifier is best characterized by a transconductance amplifier

(i)



$$r_{in} = \infty$$

$$r_{out} = r_{o2} \parallel \frac{r_{o1} + r_{o3}}{g_{m1} \cdot r_{o1}} = r_{o2} \parallel \frac{2 \cdot r_{o1}}{g_{m1} \cdot r_{o1}}$$

$$r_{out} \approx \frac{2}{g_{m1}}$$

$r_{in}$  is high; thus, voltage in

$r_{out}$  is low; thus, voltage out

Hence, amplifier is best characterized by a voltage amplifier

### Reference

Meghdad Hajimorad (“Amin”). Year 2004

↳ Original version for EE 105 Midterm Review.

Bill Hung. 16 August 2006

↳ Simplified and added-picture version for EE 40 Final Review